


2N4416,A

TO-72



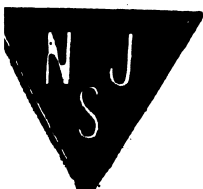
JFET
VHF/UHF AMPLIFIER
N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	30	Vdc
Drain-Gate Voltage	V _{DG}	35 30	Vdc
Gate-Source Voltage	V _{GS}	30	Vdc
Gate Current	I _G	10	mAdc
Total Device Dissipation (at T _A = 25°C Derate above 25°C)	P _D	300 1.71	mW mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I _G = 1.0 μAdc, V _{DS} = 0)	V _{(BR)GSS}	30 35	—	Vdc
Gate Reverse Current (V _{GS} = 20 Vdc, V _{DS} = 0) (V _{GS} = 20 Vdc, V _{DS} = 0, T _A = +150°C)	I _{GSS}	—	100 200	pAdc
Gate Source Cutoff Voltage (I _D = 1.0 nAdc, V _{DS} = 15 Vdc)	V _{GS(off)}	—	6.0	Vdc
Gate Source Voltage (I _D = 0.5 mAdc, V _{DS} = 15 Vdc)	V _{GS}	1.0	5.5	Vdc
Gate-Source Forward Voltage (I _G = 1.0 mAdc, V _{DS} = 0)	V _{GS(f)}	—	1.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current(1) (V _{DS} = 15 Vdc, V _{GS} = 0)	I _{DSS}	5.0	15	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance(1) (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	Y _{fs}	4500	7500	μmhos
Real Part of Forward Transfer Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 400 MHz)	Y _{fs(real)}	4000	—	μmhos
Real Part of Input Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 100 MHz) (V _{DS} = 15 Vdc, V _{GS} = 0, f = 400 MHz)	Y _{is(real)}	—	100 1000	μmhos
Output Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	Y _{os}	—	50	μmhos
Real Part of Output Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 100 MHz) (V _{DS} = 15 Vdc, V _{GS} = 0, f = 400 MHz)	Y _{os(real)}	—	75 100	μmhos
Imaginary Part of Input Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 100 MHz) (V _{DS} = 15 Vdc, V _{GS} = 0, f = 400 MHz)	Y _{is(imag)}	—	2500 10,000	μmhos
Imaginary Part of Output Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 100 MHz) (V _{DS} = 15 Vdc, V _{GS} = 0, f = 400 MHz)	Y _{os(imag)}	—	1000 4000	μmhos



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ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Input Capacitance ($V_{DS} = 15\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{iss}	—	4.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{rss}	—	0.8	pF
Common Source Output Capacitance ($V_{DS} = 15\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{oss}	—	2.0	pF

FUNCTIONAL CHARACTERISTICS

Noise Figure (Figures 3 and 4) ($V_{DS} = 15\text{ Vdc}$, $I_D = 5.0\text{ mAdc}$, $R_G = 1000\text{ Ohms}$, $f = 100\text{ MHz}$) ($V_{DS} = 15\text{ Vdc}$, $I_D = 5.0\text{ mAdc}$, $R_G = 1000\text{ Ohms}$, $f = 400\text{ MHz}$)	NF	— —	2.0 4.0	dB
Small-Signal Power Gain Common Source (Figure 1) ($V_{DS} = 15\text{ Vdc}$, $I_D = 5.0\text{ mAdc}$, $f = 100\text{ MHz}$) ($V_{DS} = 15\text{ Vdc}$, $I_D = 5.0\text{ mAdc}$, $f = 400\text{ MHz}$)	G_{ps}	18 10	— —	dB

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 1.0\%$.